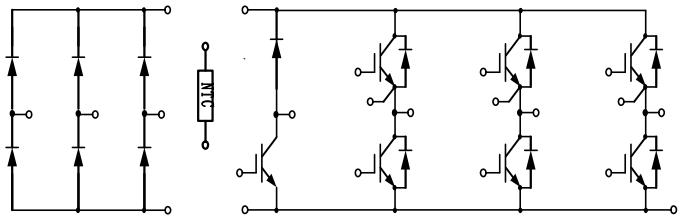
PIM IGBT Module

电气特性:

- 1200V 沟槽栅/场终止工艺
- 低开关损耗
- 正温度系数

典型应用:

- 变频器
- 伺服
- 逆变器



V_{CES} =1200V，$I_{C\ nom}$ =75A / I_{CRM} =150A

IGBT, 逆变器 / IGBT, Inverter

最大额定值 / Maximum Ratings

Parameter	Conditions	Symbol	Value	Unit
集电极-发射极电压 Collector-Emitter voltage	T_{vj}=25°C	V_{CES}	1200	V
连续集电极直流电流 Continuous DC collector current	T_C=100°C, $T_{vj\ max}$=175°C	$I_{C\ nom}$	75	A
集电极重复峰值电流 Repetitive peak collector current	t_P=1 ms	I_{CRM}	150	A
总功率损耗 Total power dissipation	T_C = 25°C, $T_{vj\ max}$ = 175°C	P_{tot}	380	W
栅极-发射极电压 Gate emitter voltage		V_{GE}	±20	V

特征值 / Characteristic Values

Parameter	Conditions		Symbol	Value			Unit
				Min.	Typ.	Max.	
集电极-发射极饱和电压 Collector-Emitter saturation voltage	V_{GE}=15V, I_C=75A V_{GE}=15V, I_C=75A V_{GE}=15V, I_C=75A	T_{vj}=25°C T_{vj}=125°C T_{vj}=150°C	V_{CEsat}		2.26 2.58 2.76	2.60	V
栅极-发射极阈值电压 Gate-Emitter threshold voltage	I_C=2.4mA, V_{GE}= V_{CE}	T_{vj}=25°C	$V_{GE(th)}$	5.20	5.70	6.40	

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内部栅极电阻 Internal gate resistor		R_{Gint}		6.20		Ω
输入电容 Input capacitance	f=1MHz, V_{CE}=25 V, V_{GE}=0 V T_{vj}=25°C	C_{ies}		5.07		nF
反向传输电容 Reverse transfer capacitance		C_{res}		0.24		
集电极-发射极截止电流 Collector-emitter cut-off current	V_{CE}=1200V , V_{GE}= 0 V T_{vj}=25°C	I_{CES}			1.0	mA
栅极-发射极漏电流 Gate-emitter leakage current	V_{CE}=0 V, V_{GE}= 20 V T_{vj}=25°C	I_{GES}			100	nA
开通延迟时间 Turn-on delay time	I_C=75A, V_{CE}=600 V T_{vj}=25°C V_{GE}=±15 V, R_G=1Ω T_{vj}=125°C (电感负载) / (inductive load) T_{vj}=150°C	$t_{d\,on}$		82 89 92		ns
上升时间 Rise time	I_C=75A, V_{CE}=600 V T_{vj}=25°C V_{GE}=±15 V, R_G=1Ω T_{vj}=125°C (电感负载) / (inductive load) T_{vj}=150°C	t_r		39 44 46		
关断延迟时间 Turn-off delay time	I_C=75A, V_{CE}=600 V T_{vj}=25°C V_{GE}=±15 V, R_G=1Ω T_{vj}=125°C (电感负载) / (inductive load) T_{vj}=150°C	$t_{d\,off}$		253 306 322		
下降时间 Fall time	I_C=75A, V_{CE}=600 V T_{vj}=25°C V_{GE}=±15 V, R_G=1Ω T_{vj}=125°C (电感负载) / (inductive load) T_{vj}=150°C	t_f		188 175 172		
开通损耗能量（每脉冲） Turn-on energy loss per pulse	I_C=75A, V_{CE}=600 V T_{vj}=25°C V_{GE}=±15 V, R_G=1Ω T_{vj}=125°C (电感负载) / (inductive load) T_{vj}=150°C	E_{on}		4.73 7.95 9.65		mJ
关断损耗能量（每脉冲） Turn-off energy loss per pulse	I_C=75A, V_{CE}=600 V T_{vj}=25°C V_{GE}=±15 V, R_G=1Ω T_{vj}=125°C (电感负载) / (inductive load) T_{vj}=150°C	E_{off}		5.06 6.42 6.88		
短路数据 SC data	V_{GE}≤15V, Vcc=800V V_{CEmax}=V_{CES}-L_{sCE}·di/dt t_P≤10us, T_{vj}=150°C	I_{SC}		355		A
结-外壳热阻 Thermal resistance, junction to case	每个 IGBT / per IGBT	R_{thJC}			0.39	K/W
在开关状态下温度 Temperature under switching conditions		$T_{vj\,op}$	-40		150	°C

二极管，逆变器 / Diode, Inverter

最大额定值 / Maximum Ratings

Parameter	Conditions	Symbol	Value	Unit
反向重复峰值电压 Repetitive peak reverse voltage	T_{vj}=25°C	V_{RRM}	1200	V
连续正向直流电流 Continuous DC forward current		I_F	75	A
正向重复峰值电流 Repetitive peak forward current	t_p=1ms	I_{FRM}	150	A
I^2t 值 I^2t-value	t_p=10ms，sin180°，T_j=125°C	I^2t	968	A^2s

特征值 / Characteristic Values

Parameter	Conditions	Symbol	Value			Unit
			Min.	Typ.	Max.	
正向电压 Forward voltage	I_F=75A, V_{GE}=0V, T_{vj}=25°C I_F=75A, V_{GE}=0V, T_{vj}=125°C I_F=75A, V_{GE}=0V, T_{vj}=150°C	V_F		2.37 2.16 2.15	2.80	V
反向恢复峰值电流 Peak reverse recovery current	I_F=75A, -di$_F$/dt=1325A/µs(T_{vj}=150°C) V_R=600V, V_{GE}=-15V T_{vj}=25°C T_{vj}=125°C T_{vj}=150°C	I_{RM}		51 78 85		A
恢复电荷 Recovered charge	I_F=75A, -di$_F$/dt=1325A/µs(T_{vj}=150°C) V_R=600V, V_{GE}=-15V T_{vj}=25°C T_{vj}=125°C T_{vj}=150°C	Q_r		5.01 12.03 15.04		µC
反向恢复损耗（每脉冲） Reverse recovered energy	I_F=75A, -di$_F$/dt=1325A/µs(T_{vj}=150°C) V_R=600V, V_{GE}=-15V T_{vj}=25°C T_{vj}=125°C T_{vj}=150°C	E_{rec}		1.48 3.48 4.43		mJ
结-外壳热阻 Thermal resistance, junction to case	每个二极管 / per diode	R_{thJC}			0.62	K/W
在开关状态下温度 Temperature under switching conditions		$T_{vj\ op}$	-40		150	°C

二极管，整流器 / Diode，Rectifier

最大额定值 / Maximum Ratings

Parameter	Conditions	Symbol	Value	Unit
反向重复峰值电压 Repetitive peak reverse voltage	T_{vj}=25°C	V_{RRM}	1800	V
反向不重复峰值电压 Non-Repetitive peak reverse voltage	T_{vj}=25°C，I_{RRM}=10µA	V_{RSM}	2000	V
最大正向平均电流 Maximum Average Forward Current		$I_{F(AV)}$	70	A
正向浪涌电流 Surge forward current	t_p=10ms，sin180°，T_{vj}=25°C	I_{FSM}	840	A
I^2t 值 I^2t-value	t_p=10ms，sin180°，T_{vj}=25°C	I^2t	3528	A^2s

特征值 / Characteristic Values

Parameter	Conditions	Symbol	Value			Unit
			Min.	Typ.	Max.	
正向电压 Forward voltage	I_F=70A, T_{vj}=25°C	V_F			1.2	V
反向电流 Reverse current	V_R=V_{RRM}, T_{vj}=25°C	I_R			10	µA
在开关状态下温度 Temperature under switching conditions		$T_{vj\ op}$	-40		150	°C

IGBT，制动-斩波器 / IGBT, Brake-Chopper

最大额定值 / Maximum Ratings

Parameter	Conditions	Symbol	Value	Unit
集电极-发射极电压 Collector-Emitter voltage	T_{vj}=25°C	V_{CES}	1200	V
连续集电极直流电流 Continuous DC collector curren	T_C=100°C, $T_{vj\ max}$=175°C	$I_{C\ nom}$	50	A
集电极重复峰值电流 Repetitive peak collector current	t_P=1 ms	I_{CRM}	100	A
总功率损耗 Total power dissipation	T_C = 25°C, $T_{vj\ max}$ = 175°C	P_{tot}	270	W
栅极-发射极电压 Gate emitter voltage		V_{GE}	±20	V

特征值 / Characteristic Values

Parameter	Conditions		Symbol	Value			Unit
				Min.	Typ.	Max.	
集电极-发射极饱和电压 Collector-Emitter saturation voltage	V_{GE}=15V, I_C=50A V_{GE}=15V, I_C=50A V_{GE}=15V, I_C=50A	T_{vj}=25°C T_{vj}=125°C T_{vj}=150°C	V_{CEsat}		2.50 3.02 3.12	2.80	V
栅极-发射极阈值电压 Gate-Emitter threshold voltage	I_C=1.6mA, V_{GE}= V_{CE}	T_{vj}=25°C	$V_{GE(th)}$	5.20	5.70	6.40	
内部栅极电阻 Internal gate resistor			R_{Gint}		2.70		Ω
输入电容 Input capacitance	f=1MHz, V_{CE}=25 V, V_{GE}=0 V	T_{vj}=25°C	C_{ies}		3.72		nF
反向传输电容 Reverse transfer capacitance			C_{res}		0.13		
集电极-发射极截止电流 Collector-emitter cut-off current	V_{CE}=1200V , V_{GE}= 0 V	T_{vj}=25°C	I_{CES}			1	mA
栅极-发射极漏电流 Gate-emitter leakage current	V_{CE}=0 V, V_{GE}= 20 V	T_{vj}=25°C	I_{GES}			100	nA
开通延迟时间 Turn-on delay time	I_C=50A, V_{CE}=600 V V_{GE}=±15 V, R_G=15Ω (电感负载) / (inductive load)	T_{vj}=25°C T_{vj}=125°C T_{vj}=150°C	$t_{d\ on}$		58 59 60		ns
上升时间 Rise time	I_C=50A, V_{CE}=600 V V_{GE}=±15 V, R_G=15Ω (电感负载) / (inductive load)	T_{vj}=25°C T_{vj}=125°C T_{vj}=150°C	t_r		49 54 54		
关断延迟时间 Turn-off delay time	I_C=50A, V_{CE}=600 V V_{GE}=±15 V, R_G=15Ω (电感负载) / (inductive load)	T_{vj}=25°C T_{vj}=125°C T_{vj}=150°C	$t_{d\ off}$		172 206 215		
下降时间 Fall time	I_C=50A, V_{CE}=600 V V_{GE}=±15 V, R_G=15Ω (电感负载) / (inductive load)	T_{vj}=25°C T_{vj}=125°C T_{vj}=150°C	t_f		163 212 217		
开通损耗能量（每脉冲） Turn-on energy loss per pulse	I_C=50A, V_{CE}=600 V V_{GE}=±15 V, R_G=15Ω	T_{vj}=25°C T_{vj}=125°C	E_{on}		3.63 5.69		mJ

	(电感负载) / (inductive load) T_{vj}=150°C			6.72		
关断损耗能量（每脉冲） Turn-off energy loss per pulse	I_C=50A, V_{CE}=600 V T_{vj}=25°C V_{GE}=±15 V, R_G=15Ω T_{vj}=125°C (电感负载) / (inductive load) T_{vj}=150°C	E_{off}		2.58 2.99 3.54		
短路数据 SC data	V_{GE}≤15V, Vcc=800V V_{CEmax}=V_{CES}-L_{sCE}·di/dt t_P≤10us, T_{vj}=150°C	I_{SC}		155		A
结-外壳热阻 Thermal resistance, junction to case	每个 IGBT / per IGBT	R_{thJC}			0.54	K/W
在开关状态下温度 Temperature under switching conditions		$T_{vj\ op}$	-40		150	°C

二极管，制动-斩波器 / Diode, Brake-Chopper

最大额定值 / Maximum Ratings

Parameter	Conditions	Symbol	Value	Unit
反向重复峰值电压 Repetitive peak reverse voltage	T_{vj}=25°C	V_{RRM}	1200	V
连续正向直流电流 Continuous DC forward current		I_F	25	A
正向重复峰值电流 Repetitive peak forward current	t_p=1ms	I_{FRM}	50	A
I^2t 值 I^2t-value	t_p=10ms, sin180°， T_{vj}=125 °C	I^2t	98	A^2s

特征值 / Characteristic Values

Parameter	Conditions		Symbol	Value			Unit
				Min.	Typ.	Max.	
正向电压 Forward voltage	I_F=25A, V_{GE}=0V I_F=25A, V_{GE}=0V I_F=25A, V_{GE}=0V	T_{vj}=25°C T_{vj}=125°C T_{vj}=150°C	V_F		2.26 1.88 1.74	2.70	V
反向恢复峰值电流 Peak reverse recovery current	I_F=25A, -di$_F$/dt=673A/µs(T_{vj}=150°C) V_R=600V, V_{GE}=-15V	T_{vj}=25°C T_{vj}=125°C T_{vj}=150°C	I_{RM}		16 26 27		A
恢复电荷 Recovered charge	I_F=25A, -di$_F$/dt=673A/µs(T_{vj}=150°C) V_R=600V, V_{GE}=-15V	T_{vj}=25°C T_{vj}=125°C T_{vj}=150°C	Q_r		1.60 3.92 5.08		µC
反向恢复损耗（每脉冲） Reverse recovered energy	I_F=25A, -di$_F$/dt=673A/µs(T_{vj}=150°C) V_R=600V, V_{GE}=-15V	T_{vj}=25°C T_{vj}=125°C T_{vj}=150°C	E_{rec}		0.56 1.33 1.75		mJ
结-外壳热阻 Thermal resistance, junction to case	每个二极管 / per diode		R_{thJC}			1.35	K/W
在开关状态下温度 Temperature under switching conditions			$T_{vj\ op}$	-40		150	°C

负温度系数热敏电阻 / NTC-Thermistor

特征值 / Characteristic Values

Parameter	Conditions	Symbol	Value			Unit
			Min.	Typ.	Max.	
额定电阻值 Rated resistances	T_c=25°C，±5%	R_{25}		5.0		KΩ
B-值 B-value	±2%	$B_{25/50}$		3375		K

模块 / Module

Parameter	Conditions	Symbol	Value			Unit
绝缘测试电压 Isolation test voltage	RMS, f=50Hz, t=1min	V_{ISOL}		2500		V
内部绝缘 Internal isolation				Al_2O_3		
储存温度 Storage temperature		T_{stg}	-40		125	°C
模块安装的扭矩 Mounting torque for modul mounting		M	3.0		6.0	Nm
重量 Weight		W		300		g

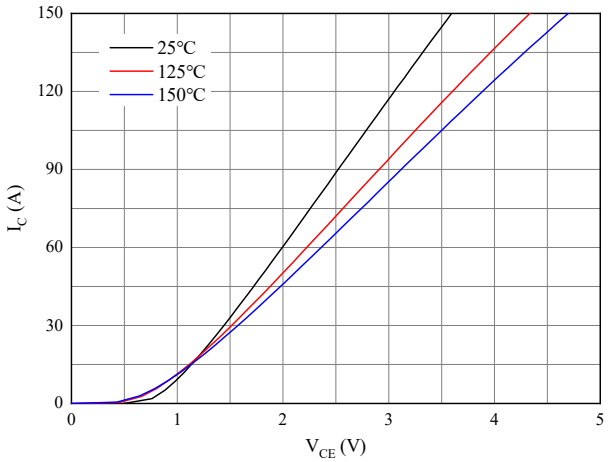


图 1. 典型输出特性 (V_{GE}=15V)

Figure 1. Typical output characteristics (V_{GE}=15V)

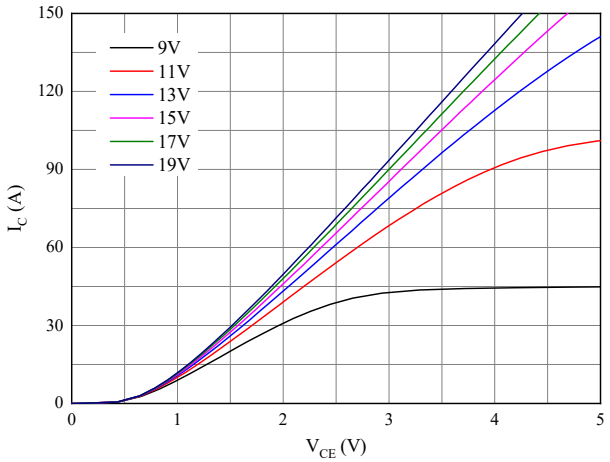


图 2. 典型输出特性 (T_{vj}=150℃)

Figure 2. Typical output characteristics (T_{vj}=150℃)

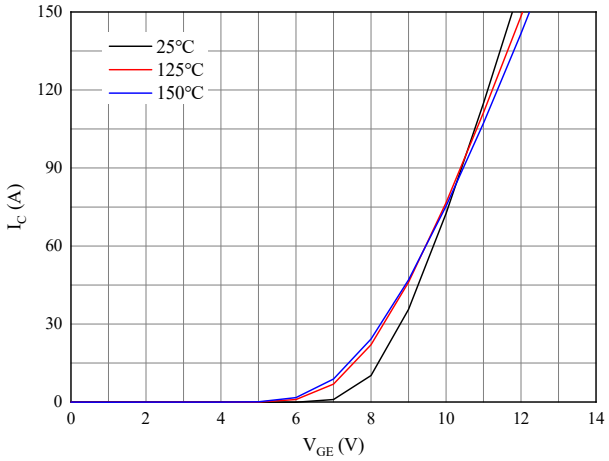


图 3. 典型传输特性(V_{CE}=20V)

Figure 3. Typical transfer characteristic(V_{CE}=20V)

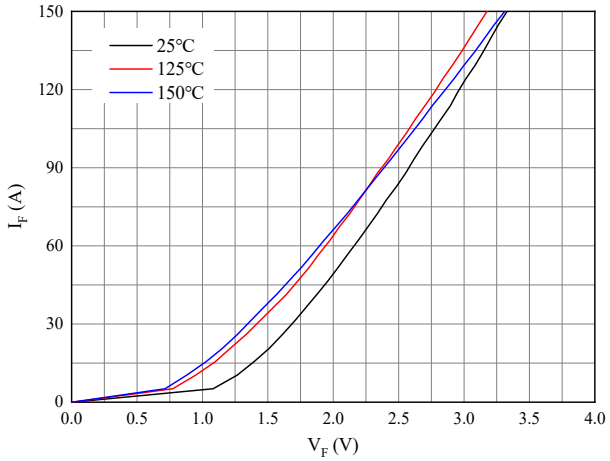


图 4. 正向偏压特性 二极管

Figure 4. Forward characteristic of Diode

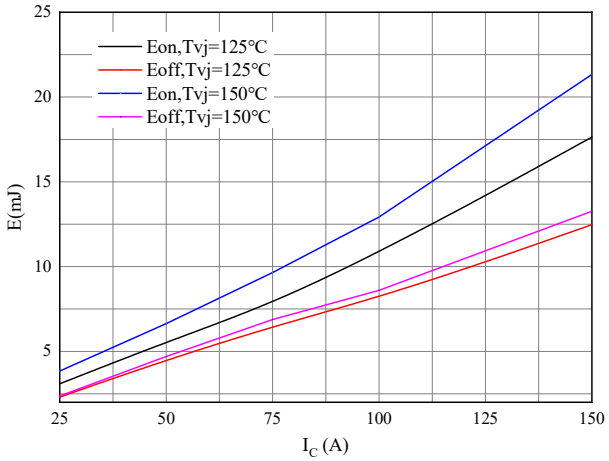


图 5. 开关损耗 逆变器

Figure 5. Switching losses of IGBT

VGE=±15V, RGon=1Ω, RGoff=1Ω, VCE=600V

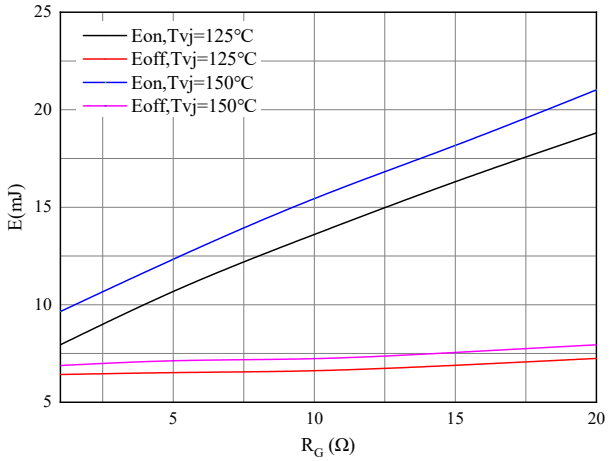


图 6. 开关损耗 逆变器

Figure 6. Switching losses of IGBT

VGE=±15V, IC=75A, VCE=600V

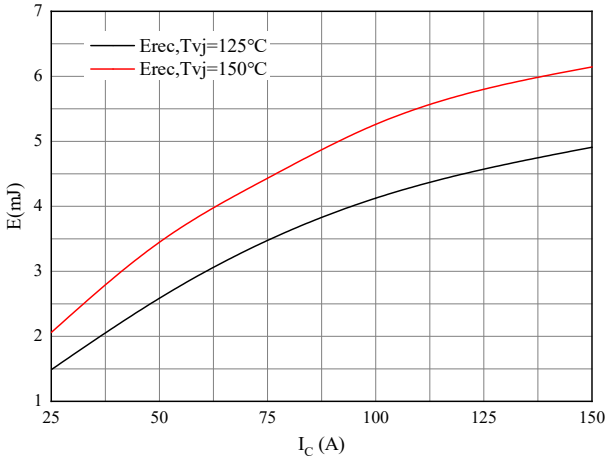


图 7. 开关损耗 二极管

Figure 7. Switching losses of Diode

RGon=1Ω, VCE=600V

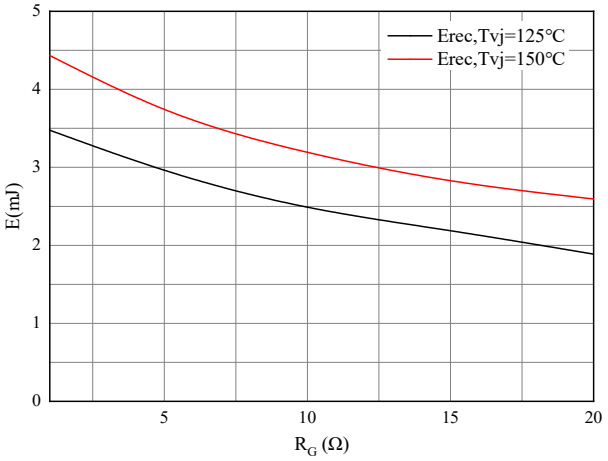


图 8. 开关损耗 二极管

Figure 8. Switching losses of Diode

IF=75A, VCE=600V

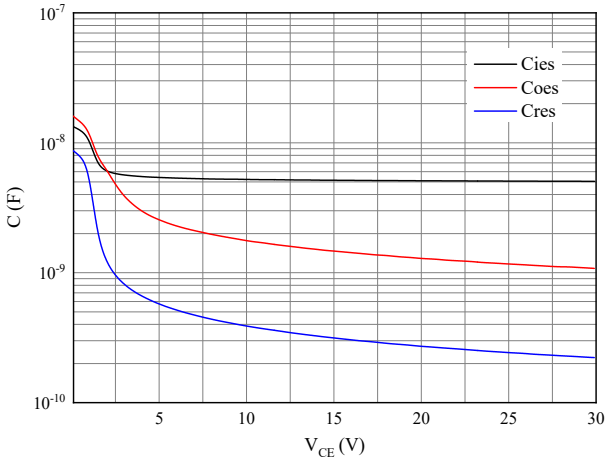


图 9. 电容特性

Figure 9. Capacitance characteristic

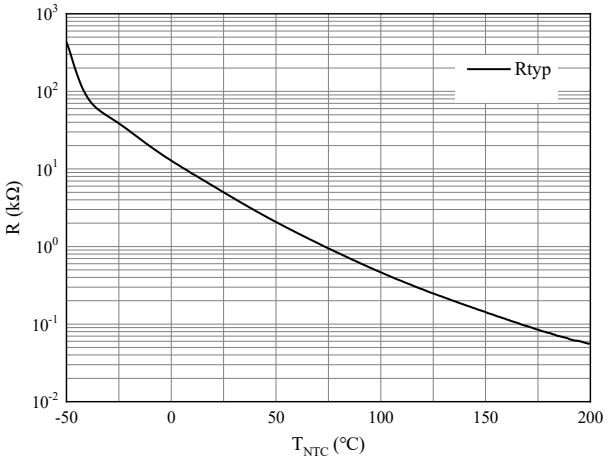
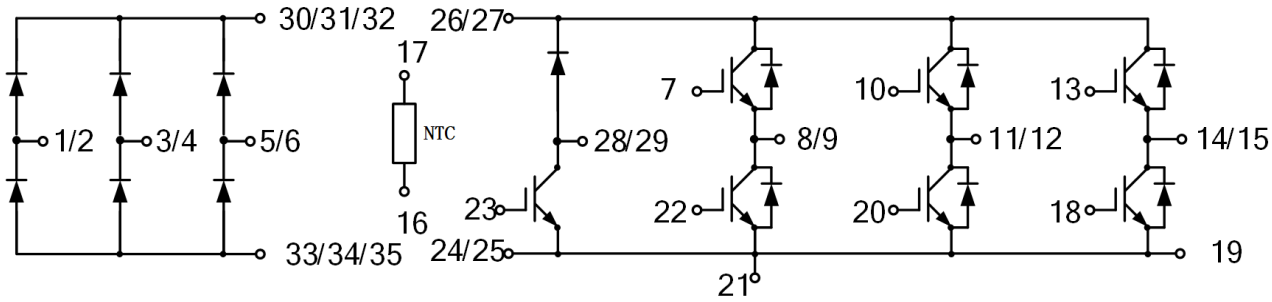


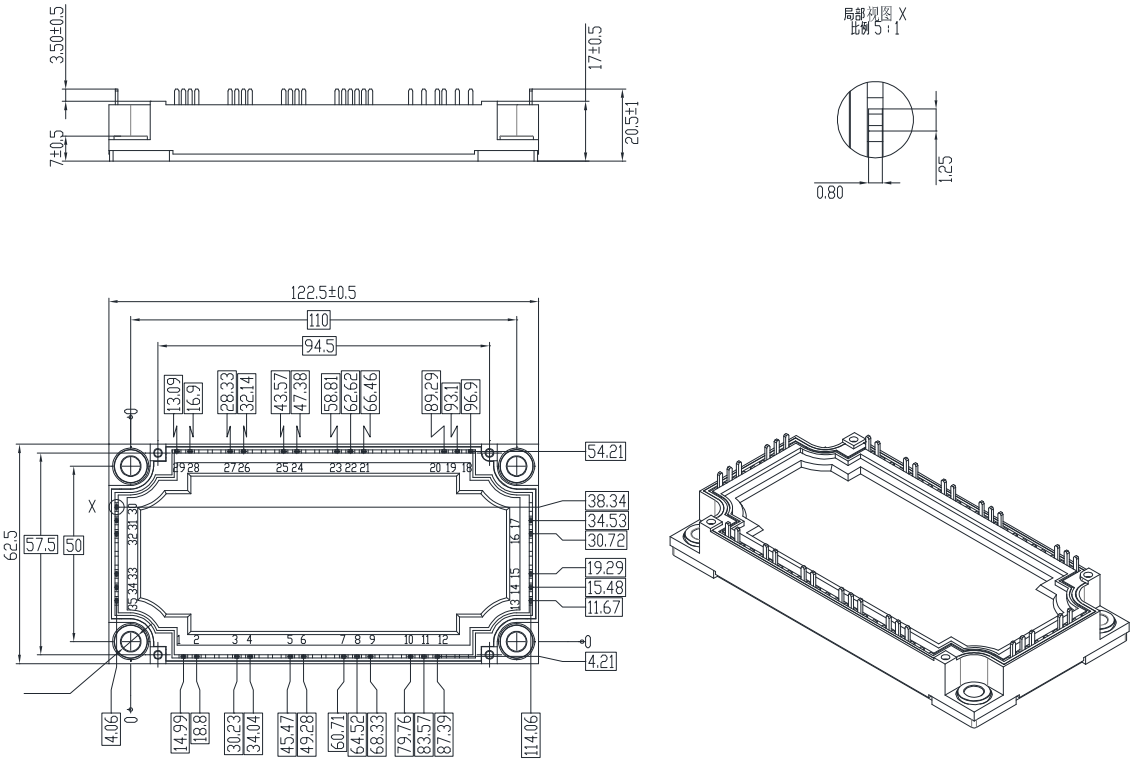
图 10. 负温系数热敏电阻 温度特性

Figure 10. NTC-Themistor-temperature characteristic

接线图 / Circuit diagram



封装尺寸 / Package outlines



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